

### Amendments to the Abstract

Please amend the Abstract as follows:

~~Transistors and~~ Fabrication methods are presented in which a semiconductor body is deposited in a cavity of a temporary form structure above a semiconductor starting structure. The formed semiconductor body can be epitaxial silicon deposited in the form cavity over a silicon substrate, and includes three body portions, two of which are doped to form source/drains, and the other forming a transistor channel that overlies the starting structure. A gate structure is formed along one or more sides of the channel body portion to create a MOS transistor.